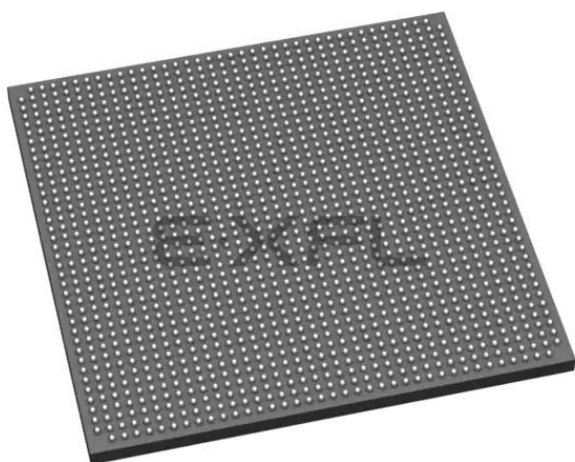




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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details

Product Status	Active
Architecture	MCU, FPGA
Core Processor	Quad ARM® Cortex®-A53 MPCore™ with CoreSight™, Dual ARM®Cortex™-R5 with CoreSight™, ARM Mali™ -400 MP2
Flash Size	-
RAM Size	256KB
Peripherals	DMA, WDT
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Speed	533MHz, 600MHz, 1.3GHz
Primary Attributes	Zynq®UltraScale+™ FPGA, 653K+ Logic Cells
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	1517-BBGA, FCBGA
Supplier Device Package	1517-FCBGA (40x40)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xczu11eg-2ffvf1517i

Table 2: Recommended Operating Conditions⁽¹⁾⁽²⁾ (Cont'd)

Symbol	Description	Min	Typ	Max	Units
$V_{CCO}^{(8)}$	Supply voltage for HD I/O banks.	1.140	–	3.400	V
	Supply voltage for HP I/O banks.	0.950	–	1.900	V
$V_{CCAUX_IO}^{(9)}$	Auxiliary I/O supply voltage.	1.746	1.800	1.854	V
$V_{IN}^{(10)}$	I/O input voltage.	–0.200	–	$V_{CCO} + 0.200$	V
$I_{IN}^{(11)}$	Maximum current through any PL or PS pin in a powered or unpowered bank when forward biasing the clamp diode.	–	–	10	mA
GTH or GTY Transceiver					
$V_{MGTAVCC}^{(12)}$	Analog supply voltage for the GTH or GTY transceiver.	0.873	0.900	0.927	V
$V_{MGTAVTT}^{(12)}$	Analog supply voltage for the GTH or GTY transmitter and receiver termination circuits.	1.164	1.200	1.236	V
$V_{MGTVCCAUX}^{(12)}$	Auxiliary analog QPLL voltage supply for the transceivers.	1.746	1.800	1.854	V
$V_{MGTAVTTRCAL}^{(12)}$	Analog supply voltage for the resistor calibration circuit of the GTH or GTY transceiver column.	1.164	1.200	1.236	V
VCU					
V_{CCINT_VCU}	Internal supply voltage for the VCU.	0.825	0.850	0.876	V
	For -1LI and -2LE ($V_{CCINT} = 0.72V$) devices: Internal supply voltage for the VCU.	0.825	0.850	0.876	V
	For -3E devices: Internal supply voltage for the VCU.	0.873	0.900	0.927	V

Table 2: Recommended Operating Conditions⁽¹⁾⁽²⁾ (Cont'd)

Symbol	Description	Min	Typ	Max	Units
PL System Monitor					
V _{CCADC}	PL System Monitor supply relative to GNDADC.	1.746	1.800	1.854	V
V _{REFP}	PL System Monitor externally supplied reference voltage relative to GNDADC.	1.200	1.250	1.300	V
Temperature					
T _j ⁽¹³⁾	Junction temperature operating range for extended (E) temperature devices. ⁽¹⁴⁾	0	–	100	°C
	Junction temperature operating range for industrial (I) temperature devices.	–40	–	100	°C
	Junction temperature operating range for eFUSE programming.	–40	–	125	°C

Notes:

- All voltages are relative to GND.
- For the design of the power distribution system consult *UltraScale Architecture PCB Design Guide* ([UG583](#)).
- V_{CC_PSINTFP_DDR} must be tied to V_{CC_PSINTFP}.
- Includes V_{CCO_PSDDR} of 1.2V, 1.35V, 1.5V at ±5% and 1.1V +0.07V/–0.04V depending upon the tolerances required by specific memory standards.
- Applies to all PS I/O supply banks. Includes V_{CCO_PSIO} of 1.8V, 2.5V, and 3.3V at ±5%.
- If the battery-backed RAM or RTC is not used, connect V_{CC_PSBATT} to GND or V_{CC_PSAUX}. The V_{CC_PSAUX} maximum of 1.89V is acceptable on an unused V_{CC_PSBATT}.
- V_{CCINT_IO} must be connected to V_{CCBRAM}.
- Includes V_{CCO} of 1.0V (HP I/O only), 1.2V, 1.35V, 1.5V, 1.8V, 2.5V (HD I/O only) at ±5%, and 3.3V (HD I/O only) at +3/–5%.
- V_{CCAUX_IO} must be connected to V_{CCAUX}.
- The lower absolute voltage specification always applies.
- A total of 200 mA per bank should not be exceeded.
- Each voltage listed requires filtering as described in *UltraScale Architecture GTH Transceiver User Guide* ([UG576](#)) or *UltraScale Architecture GTY Transceiver User Guide* ([UG578](#)).
- Xilinx recommends measuring the T_j of a device using the system monitor as described in the *UltraScale Architecture System Monitor User Guide* ([UG580](#)). The SYSMON temperature measurement errors (that are described in [Table 69](#) and [Table 124](#)) must be accounted for in your design. For example, when using the PL system monitor with an external reference of 1.25V, when SYSMON reports 97°C, there is a measurement error ±3°C. A reading of 97°C is considered the maximum adjusted T_j (100°C – 3°C = 97°C).
- Devices labeled with the speed/temperature grade of -2LE normally operate under Extended (E) temperature grade specifications with a maximum junction temperature of 100°C. However, E temperature grade devices can operate for a limited time at a junction temperature of 110°C. Timing parameters adhere to the same speed file at 110°C as they do at 100°C, regardless of operating voltage (nominal voltage of 0.85V or a low-voltage of 0.72V). Operation at T_j = 110°C is limited to 1% of the device lifetime and can occur sequentially or at regular intervals as long as the total time does not exceed 1% of the device lifetime.

Table 4: DC Characteristics Over Recommended Operating Conditions (Cont'd)

Symbol	Description	Min	Typ ⁽¹⁾	Max	Units
I_{CC_PSBATT} ⁽⁴⁾⁽⁵⁾	Battery supply current at $V_{CC_PSBATT} = 1.50V$, RTC enabled.	–	–	3650	nA
	Battery supply current at $V_{CC_PSBATT} = 1.50V$, RTC disabled.	–	–	650	nA
	Battery supply current at $V_{CC_PSBATT} = 1.20V$, RTC enabled.	–	–	3150	nA
	Battery supply current at $V_{CC_PSBATT} = 1.20V$, RTC disabled.	–	–	150	nA
I_{PSFS} ⁽⁶⁾	PS V_{CC_PSAUX} additional supply current during eFUSE programming.	–	–	115	mA
<i>Calibrated programmable on-die termination (DCI) in HP I/O banks⁽⁸⁾ (measured per JEDEC specification)</i>					
R ⁽⁹⁾	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where $ODT = RTT_{40}$.	–10% ⁽⁷⁾	40	+10% ⁽⁷⁾	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where $ODT = RTT_{48}$.	–10% ⁽⁷⁾	48	+10% ⁽⁷⁾	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where $ODT = RTT_{60}$.	–10% ⁽⁷⁾	60	+10% ⁽⁷⁾	Ω
	Programmable input termination to V_{CCO} where $ODT = RTT_{40}$.	–10% ⁽⁷⁾	40	+10% ⁽⁷⁾	Ω
	Programmable input termination to V_{CCO} where $ODT = RTT_{48}$.	–10% ⁽⁷⁾	48	+10% ⁽⁷⁾	Ω
	Programmable input termination to V_{CCO} where $ODT = RTT_{60}$.	–10% ⁽⁷⁾	60	+10% ⁽⁷⁾	Ω
	Programmable input termination to V_{CCO} where $ODT = RTT_{120}$.	–10% ⁽⁷⁾	120	+10% ⁽⁷⁾	Ω
	Programmable input termination to V_{CCO} where $ODT = RTT_{240}$.	–10% ⁽⁷⁾	240	+10% ⁽⁷⁾	Ω
<i>Uncalibrated programmable on-die termination in HP I/Os banks (measured per JEDEC specification)</i>					
R ⁽⁹⁾	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where $ODT = RTT_{40}$.	–50%	40	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where $ODT = RTT_{48}$.	–50%	48	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where $ODT = RTT_{60}$.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where $ODT = RTT_{40}$.	–50%	40	+50%	Ω
	Programmable input termination to V_{CCO} where $ODT = RTT_{48}$.	–50%	48	+50%	Ω
	Programmable input termination to V_{CCO} where $ODT = RTT_{60}$.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where $ODT = RTT_{120}$.	–50%	120	+50%	Ω
	Programmable input termination to V_{CCO} where $ODT = RTT_{240}$.	–50%	240	+50%	Ω
<i>Uncalibrated programmable on-die termination in HD I/O banks (measured per JEDEC specification)</i>					
R ⁽⁹⁾	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where $ODT = RTT_{48}$.	–50%	48	+50%	Ω
Internal V_{REF}	50% V_{CCO}	$V_{CCO} \times 0.49$	$V_{CCO} \times 0.50$	$V_{CCO} \times 0.51$	V
	70% V_{CCO}	$V_{CCO} \times 0.69$	$V_{CCO} \times 0.70$	$V_{CCO} \times 0.71$	V

Table 11: Power Supply Ramp Time (Cont'd)

Symbol	Description	Min	Max	Units
$T_{V_{CCO_PSDDR}}$	Ramp time from GND to 95% of V_{CCO_PSDDR} .	0.2	40	ms
$T_{V_{CC_PSDDR_PLL}}$	Ramp time from GND to 95% of $V_{CC_PSDDR_PLL}$.	0.2	40	ms
$T_{V_{CCO_PSIO}}$	Ramp time from GND to 95% of V_{CCO_PSIO} .	0.2	40	ms

DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

PS I/O Levels

Table 12: PS MIO and CONFIG DC Input and Output Levels⁽¹⁾

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
LVC MOS33	-0.300	0.800	2.000	V_{CCO_PSIO}	0.40	2.40	12	-12
LVC MOS25	-0.300	0.700	1.700	$V_{CCO_PSIO} + 0.30$	0.70	1.70	12	-12
LVC MOS18	-0.300	35% V_{CCO_PSIO}	65% V_{CCO_PSIO}	$V_{CCO_PSIO} + 0.30$	0.45	$V_{CCO_PSIO} - 0.45$	12	-12

Notes:

1. Tested according to relevant specifications.

Table 13: PS DDR DC Input and Output Levels⁽¹⁾

DDR Standard	V_{IL}		V_{IH}		$V_{OL}^{(2)}$	$V_{OH}^{(2)}$	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
DDR4	0.000	$V_{REF} - 0.100$	$V_{REF} + 0.100$	V_{CCO_PSDDR}	$0.8 \times V_{CCO_PSDDR} - 0.150$	$0.8 \times V_{CCO_PSDDR} + 0.150$	10	-0.1
LPDDR4	0.000	$V_{REF} - 0.100$	$V_{REF} + 0.100$	V_{CCO_PSDDR}	$0.3 \times V_{CCO_PSDDR} - 0.150$	$0.3 \times V_{CCO_PSDDR} + 0.150$	0.1	-10
DDR3	-0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	V_{CCO_PSDDR}	$0.5 \times V_{CCO_PSDDR} - 0.175$	$0.5 \times V_{CCO_PSDDR} + 0.175$	8	-8
LPDDR3	0.000	$V_{REF} - 0.100$	$V_{REF} + 0.100$	V_{CCO_PSDDR}	$0.5 \times V_{CCO_PSDDR} - 0.150$	$0.5 \times V_{CCO_PSDDR} + 0.150$	8	-8
DDR3L	-0.300	$V_{REF} - 0.090$	$V_{REF} + 0.090$	V_{CCO_PSDDR}	$0.5 \times V_{CCO_PSDDR} - 0.150$	$0.5 \times V_{CCO_PSDDR} + 0.150$	8	-8

Notes:

1. Tested according to relevant specifications.
2. DDR4 V_{OL}/V_{OH} specifications are only applicable for DQ/DQS pins.

PS Switching Characteristics

PS Clocks

Table 34: PS Reference Clock Requirements⁽¹⁾

Symbol	Description	Min	Typ	Max	Units
T _{RMSJPCLK}	PS_REF_CLK input RMS clock jitter.	–	–	3	ps
T _{PJPCLK}	PS_REF_CLK input period jitter (peak-to-peak). Number of clock cycles = 10,000	–	–	50	ps
T _{DCPCLK}	PS_REF_CLK duty cycle.	45	–	55	%
T _{RFPSCLK}	PS_REF_CLK rise time (20%–80%) and fall time (80%–20%).	–	–	2.22	ns
F _{PSCLK}	PS_REF_CLK frequency.	27	–	60	MHz

Notes:

- The values in this table are applicable to alternative PS reference clock inputs ALT_REF_CLK, AUX_REF_CLK, and VIDEO_CLK.

Table 35: PS RTC Crystal Requirements⁽¹⁾

Symbol	Description	Min	Typ	Max	Units
F _{XTAL}	Parallel resonance crystal frequency.	–	32.8	–	KHz
T _{FTXTAL}	Frequency tolerance.	–20	–	20	ppm
C _{XTAL}	Load capacitance for crystal parallel resonance.	–	12.5	–	pF
R _{ESR}	Crystal ESR (16.8 and 19.2 MHz).	–	70	–	KΩ
C _{SHUNT}	Crystal shunt capacitance.	–	1.4	–	pF

Notes:

- Required board components: Feedback resistor = 4.7 MΩ, PCB and pad capacitance = 1.5 pF, C₁ and C₂ capacitance = 21 pF.

Table 36: PS PLL Switching Characteristics

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
F _{LOCKPSPLL}	PLL maximum lock time.	100	100	100	μs
F _{PSPLLMAX}	PLL maximum output frequency.	1600	1600	1600	MHz
F _{PSPLLMIN}	PLL minimum output frequency.	750	750	750	MHz
F _{PSPLLVCOMAX}	PLL maximum VCO frequency.	3000	3000	3000	MHz
F _{PSPLLVCOMIN}	PLL minimum VCO frequency.	1500	1500	1500	MHz

PS Configuration

Table 39: Processor Configuration Access Port Switching Characteristics

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
F _{PCAPCK}	Maximum processor configuration access port (PCAP) frequency.	200	200	200	150	150	MHz

Table 40: Boundary-Scan Port Switching Characteristics

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
F _{TCK}	JTAG clock maximum frequency.	25	25	25	15	15	MHz
T _{TAPTCK} /T _{TCKTAP}	TMS and TDI setup and hold.	4.0/2.0	4.0/2.0	4.0/2.0	5.0/2.0	5.0/2.0	ns, Min
T _{TCKTDO}	TCK falling edge to TDO output.	16.1	16.1	16.1	24	24	ns, Max

Notes:

1. The test conditions are configured to the LVCMOS 3.3V I/O standard with a 12 mA drive strength.

PS DAP Interface

Table 50: DAP Interface⁽¹⁾

Symbol	Description ⁽²⁾	Min	Max	Units
$T_{PDAPDCK}$	PS DAP input setup time.	3.0	–	ns
$T_{PDAPCKD}$	PS DAP input hold time.	2.0	–	ns
$T_{PDAPCKO}$	PS DAP clock to out delay.	–	10.86	ns
$T_{PDAPCLK}$	PS DAP clock frequency.	–	44	MHz

Notes:

1. The test conditions are configured to the LVCMOS 3.3V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.
2. PS DAP interface signals connect to MIO pins.

PS UART Interface

Table 51: UART Interface⁽¹⁾

Symbol	Description	Min	Max	Units
$BAUD_{TXMAX}$	Transmit baud rate.	–	6.25	Mb/s
$BAUD_{RXMAX}$	Receive baud rate.	–	6.25	Mb/s
$F_{UART_REF_CLK}$	UART reference clock frequency.	–	100	MHz

Notes:

1. The test conditions are configured to the LVCMOS 3.3V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.

PS General Purpose I/O Interface

Table 52: General Purpose I/O (GPIO) Interface

Symbol	Description	Min	Max	Units
$T_{PWGPIOH}$	Input High pulse width.	$10 \times 1/F_{LPD_LSBUS_CTRLMAX}$	–	μs
$T_{PWGPIO L}$	Input Low pulse width.	$10 \times 1/F_{LPD_LSBUS_CTRLMAX}$	–	μs

PS Trace Interface

Table 53: Trace Interface⁽¹⁾

Symbol	Description	Min	Max	Units
T_{TCECKO}	Trace clock to output delay, all outputs.	–0.5	0.5	ns
$T_{DCTCECLK}$	Trace clock duty cycle.	45	55	%
F_{TCECLK}	Trace clock frequency.	–	125	MHz

Notes:

1. The test conditions are configured to the LVCMOS 3.3V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.

PS-GTR Transceiver

Table 56: PS-GTR Transceiver DC Specifications

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
DV _{PPIN}	Differential peak-to-peak input voltage (external AC coupled).		100	–	1200	mV
V _{IN}	Single-ended input voltage. Voltage measured at the pin referenced to GND.		75	–	V _{PS_MGTRAVCC}	mV
V _{CMIN}	Common mode input voltage.		–	0	–	mV
DV _{PPOUT}	Differential peak-to-peak output voltage. ⁽¹⁾	Transmitter output swing is set to maximum value.	800	–	–	mV
V _{CMOUTAC}	Common mode output voltage: AC coupled (equation based).		$V_{PS_MGTRAVCC} - D_{VPPOUT}/2$			mV
R _{IN}	Differential input resistance.		–	100	–	Ω
R _{OUT}	Differential output resistance.		–	100	–	Ω
R _{MGTREF}	Resistor value between calibration resistor pin to GND.		497.5	500	502.5	Ω
T _{OSKEW}	Transmitter output pair (TXP and TXN) intra-pair skew (All packages).		–	–	20	ps
C _{EXT}	Recommended external AC coupling capacitor. ⁽²⁾		–	100	–	nF

Notes:

1. The output swing and pre-emphasis levels are programmable using the attributes discussed in the *Zynq UltraScale+ MPSoC Technical Reference Manual* (UG1085), and can result in values lower than reported in this table.
2. Other values can be used as appropriate to conform to specific protocols and standards.

Table 57: PS-GTR Transceiver Clock DC Input Level Specification

Symbol	DC Parameter	Min	Typ	Max	Units
V _{IDIFF}	Differential peak-to-peak input voltage.	250	–	2000	mV
R _{IN}	Differential input resistance.	–	100	–	Ω
C _{EXT}	Required external AC coupling capacitor.	–	10	–	nF

Table 58: PS-GTR Transceiver Performance

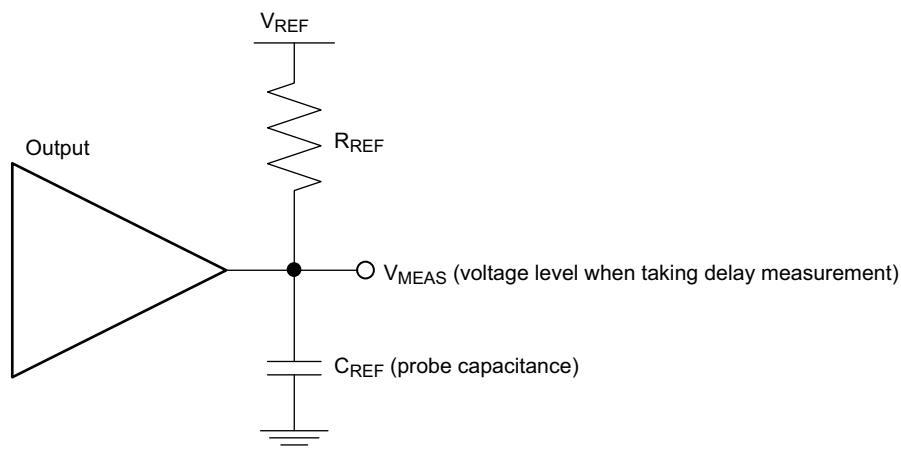
Symbol	Description	Speed Grade			Units
		-3	-2	-1	
F _{GTRMAX}	PS-GTR maximum line rate.	6.0	6.0	6.0	Gb/s
F _{GTRMIN}	PS-GTR minimum line rate.	1.25	1.25	1.25	Gb/s

Table 59: PS-GTR Transceiver PLL/Lock Time Adaptation

Symbol	Description	Min	Typ	Max	Units
T _{LOCK}	Initial PLL lock.	–	–	0.11	ms
T _{DLOCK}	Clock recovery phase acquisition and adaptation time.	–	–	24 x 10 ⁶	UI

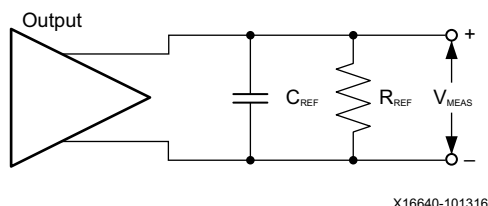
Output Delay Measurement Methodology

Output delays are measured with short output traces. Standard termination was used for all testing. The propagation delay of the trace is characterized separately and subtracted from the final measurement, and is therefore not included in the generalized test setups shown in [Figure 1](#) and [Figure 2](#).



X16654-101316

Figure 1: Single-Ended Test Setup



X16640-101316

Figure 2: Differential Test Setup

Parameters V_{REF} , R_{REF} , C_{REF} , and V_{MEAS} fully describe the test conditions for each I/O standard. The most accurate prediction of propagation delay in any given application can be obtained through IBIS simulation, using this method:

1. Simulate the output driver of choice into the generalized test setup using values from [Table 79](#).
2. Record the time to V_{MEAS} .
3. Simulate the output driver of choice into the actual PCB trace and load using the appropriate IBIS model or capacitance value to represent the load.
4. Record the time to V_{MEAS} .
5. Compare the results of [step 2](#) and [step 4](#). The increase or decrease in delay yields the actual propagation delay of the PCB trace.

Block RAM and FIFO Switching Characteristics

Table 80: Block RAM and FIFO Switching Characteristics

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
Maximum Frequency							
F _{MAX_WF_NC}	Block RAM (WRITE_FIRST and NO_CHANGE modes).	825	738	645	585	516	MHz
F _{MAX_RF}	Block RAM (READ_FIRST mode).	718	637	575	510	460	MHz
F _{MAX_FIFO}	FIFO in all modes without ECC.	825	738	645	585	516	MHz
F _{MAX_ECC}	Block RAM and FIFO in ECC configuration without PIPELINE.	718	637	575	510	460	MHz
	Block RAM and FIFO in ECC configuration with PIPELINE and Block RAM in WRITE_FIRST or NO_CHANGE mode.	825	738	645	585	516	MHz
T _{PW} ⁽¹⁾	Minimum pulse width.	495	542	543	577	578	ps
Block RAM and FIFO Clock-to-Out Delays							
T _{RCKO_DO}	Clock CLK to DOUT output (without output register).	0.91	1.02	1.11	1.46	1.53	ns, Max
T _{RCKO_DO_REG}	Clock CLK to DOUT output (with output register).	0.27	0.29	0.30	0.42	0.44	ns, Max

Notes:

1. The MMCM and PLL DUTY_CYCLE attribute should be set to 50% to meet the pulse-width requirements at the higher frequencies.

UltraRAM Switching Characteristics

The *UltraScale Architecture and Product Overview* ([DS890](#)) lists the Zynq UltraScale+ MPSoC that include this memory.

Table 81: UltraRAM Switching Characteristics

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
Maximum Frequency							
F _{MAX}	UltraRAM maximum frequency with OREG_B = True.	650	600	575	500	481	MHz
F _{MAX_ECC}	UltraRAM maximum frequency with OREG_B = False and EN_ECC_RD_B = True.	450	400	386	325	315	MHz
F _{MAX_NORPIPELINE}	UltraRAM maximum frequency with OREG_B = False and EN_ECC_RD_B = False.	550	500	478	425	408	MHz
T _{PW} ⁽¹⁾	Minimum pulse width.	650	700	730	800	832	ps
T _{RSTPW}	Asynchronous reset minimum pulse width. One cycle required.	1 clock cycle					

Notes:

1. The MMCM and PLL DUTY_CYCLE attribute should be set to 50% to meet the pulse-width requirements at the higher frequencies.

Input/Output Delay Switching Characteristics

Table 82: Input/Output Delay Switching Characteristics

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
F _{REFCLK}	REFCLK frequency for IDELAYCTRL (component mode).	300 to 800					MHz
	REFCLK frequency for BITSlice_CONTROL (native mode). ⁽¹⁾	300 to 2666.67	300 to 2666.67	300 to 2400	300 to 2400	300 to 2133	MHz
T _{MINPER_CLK}	Minimum period for IODELAY clock.	3.195	3.195	3.195	3.195	3.195	ns
T _{MINPER_RST}	Minimum reset pulse width.	52.00					ns
T _{IDELAY_RESOLUTION} / T _{ODELAY_RESOLUTION}	IDELAY/ODELAY chain resolution.	2.1 to 12					ps

Notes:

1. PLL settings could restrict the minimum allowable data rate. For example, when using a PLL with CLKOUTPHY_MODE = VCO_HALF, the minimum frequency is PLL_FVCOMIN/2.

Table 88: Global Clock Input to Output Delay Without MMCM (Far Clock Region)

Symbol	Description	Device	Speed Grade and V _{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
SSTL15 Global Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, <i>without</i> MMCM.								
T _{ICKOF_FAR}	Global clock input and output flip-flop <i>without</i> MMCM (far clock region).	XCZU2	N/A	5.27	5.68	5.80	6.13	ns
		XCZU3	N/A	5.27	5.68	5.80	6.13	ns
		XCZU4	5.07	6.06	6.61	6.23	7.10	ns
		XCZU5	5.07	6.06	6.61	6.23	7.10	ns
		XCZU6	5.38	6.49	6.97	7.14	7.59	ns
		XCZU7	5.39	6.54	7.01	7.16	7.62	ns
		XCZU9	5.38	6.49	6.97	7.14	7.59	ns
		XCZU11	6.18	7.41	8.11	7.66	8.99	ns
		XCZU15	5.38	6.49	6.96	7.19	7.71	ns
		XCZU17	6.21	7.53	8.07	8.36	8.90	ns
		XCZU19	6.21	7.53	8.07	8.36	8.90	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.

Table 89: Global Clock Input to Output Delay With MMCM

Symbol	Description	Device	Speed Grade and V _{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
SSTL15 Global Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, with MMCM.								
T _{ICKOFMMCMCC}	Global clock input and output flip-flop <i>with</i> MMCM.	XCZU2	N/A	2.22	2.43	2.96	2.94	ns
		XCZU3	N/A	2.22	2.43	2.96	2.94	ns
		XCZU4	2.47	2.47	2.78	3.04	3.35	ns
		XCZU5	2.47	2.47	2.78	3.04	3.35	ns
		XCZU6	2.15	2.15	2.36	2.86	2.86	ns
		XCZU7	2.32	2.32	2.57	3.06	3.13	ns
		XCZU9	2.15	2.15	2.36	2.86	2.86	ns
		XCZU11	2.64	2.64	2.96	3.25	3.55	ns
		XCZU15	2.18	2.18	2.38	2.88	2.90	ns
		XCZU17	2.44	2.44	2.66	3.19	3.17	ns
XCZU19	2.44	2.44	2.66	3.19	3.17	ns		

Notes:

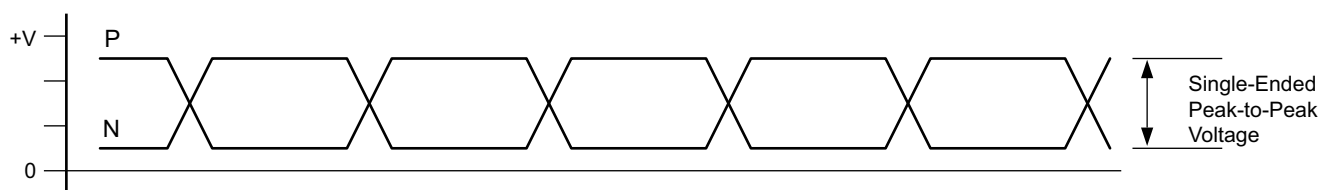
1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.
2. MMCM output jitter is already included in the timing calculation.

Table 91: Global Clock Input Setup and Hold With MMCM

Symbol	Description	Device	Speed Grade and V _{CCINT} Operating Voltages					Units	
			0.90V	0.85V		0.72V			
			-3	-2	-1	-2	-1		
Input Setup and Hold Time Relative to Global Clock Input Signal using SSTL15 Standard. ⁽¹⁾⁽²⁾⁽³⁾									
T _{PSMMCMCC_ZU2}	Global clock input and input flip-flop (or latch) with MMCM.	Setup	XCZU2	N/A	1.83	1.96	2.29	2.48	ns
T _{PHMMCMCC_ZU2}		Hold			−0.19	−0.19	0.13	0.13	ns
T _{PSMMCMCC_ZU3}		Setup	XCZU3	N/A	1.83	1.96	2.29	2.48	ns
T _{PHMMCMCC_ZU3}		Hold			−0.19	−0.19	0.13	0.13	ns
T _{PSMMCMCC_ZU4}		Setup	XCZU4	1.96	1.96	2.10	2.49	2.59	ns
T _{PHMMCMCC_ZU4}		Hold		−0.12	−0.12	−0.12	0.27	0.48	ns
T _{PSMMCMCC_ZU5}		Setup	XCZU5	1.96	1.96	2.10	2.49	2.59	ns
T _{PHMMCMCC_ZU5}		Hold		−0.12	−0.12	−0.12	0.27	0.48	ns
T _{PSMMCMCC_ZU6}		Setup	XCZU6	1.97	2.00	2.12	2.26	2.44	ns
T _{PHMMCMCC_ZU6}		Hold		−0.11	−0.11	−0.11	0.16	0.18	ns
T _{PSMMCMCC_ZU7}		Setup	XCZU7	1.91	1.91	2.02	2.45	2.70	ns
T _{PHMMCMCC_ZU7}		Hold		−0.14	−0.14	−0.14	0.37	0.38	ns
T _{PSMMCMCC_ZU9}		Setup	XCZU9	1.97	2.00	2.12	2.26	2.44	ns
T _{PHMMCMCC_ZU9}		Hold		−0.11	−0.11	−0.11	0.16	0.18	ns
T _{PSMMCMCC_ZU11}		Setup	XCZU11	2.08	2.08	2.23	2.59	2.75	ns
T _{PHMMCMCC_ZU11}		Hold		−0.08	−0.08	0.04	0.35	0.74	ns
T _{PSMMCMCC_ZU15}		Setup	XCZU15	1.96	1.99	2.12	2.26	2.44	ns
T _{PHMMCMCC_ZU15}		Hold		−0.10	−0.10	−0.10	0.17	0.19	ns
T _{PSMMCMCC_ZU17}		Setup	XCZU17	1.89	1.89	2.03	2.36	2.55	ns
T _{PHMMCMCC_ZU17}		Hold		−0.16	−0.16	−0.16	0.31	0.34	ns
T _{PSMMCMCC_ZU19}	Setup	XCZU19	1.89	1.89	2.03	2.36	2.55	ns	
T _{PHMMCMCC_ZU19}	Hold		−0.16	−0.16	−0.16	0.31	0.34	ns	

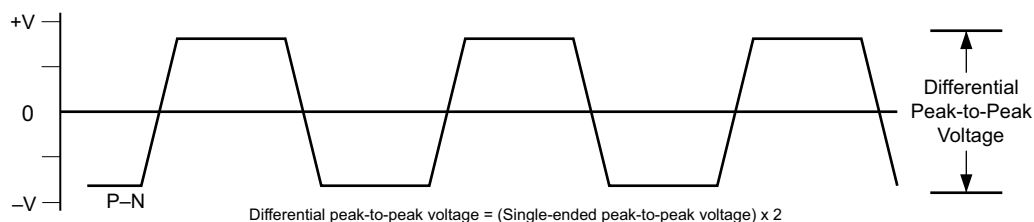
Notes:

1. Setup and hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the global clock input signal using the slowest process, slowest temperature, and slowest voltage. Hold time is measured relative to the global clock input signal using the fastest process, fastest temperature, and fastest voltage.
2. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.
3. Use IBIS to determine any duty-cycle distortion incurred using various standards.



X16653-101316

Figure 3: Single-Ended Peak-to-Peak Voltage



X16639-101316

Figure 4: Differential Peak-to-Peak Voltage

Table 95 and Table 96 summarize the DC specifications of the GTH transceivers input and output clocks in Zynq UltraScale+ MPSoC. Consult the *UltraScale Architecture GTH Transceiver User Guide* ([UG576](#)) for further details.

Table 95: GTH Transceiver Clock Input Level Specification

Symbol	DC Parameter	Min	Typ	Max	Units
V_{IDIFF}	Differential peak-to-peak input voltage.	250	–	2000	mV
R_{IN}	Differential input resistance.	–	100	–	Ω
C_{EXT}	Required external AC coupling capacitor.	–	10	–	nF

Table 96: GTH Transceiver Clock Output Level Specification

Symbol	Description	Conditions	Min	Typ	Max	Units
V_{OL}	Output Low voltage for P and N.	$R_T = 100\Omega$ across P and N signals	100	–	330	mV
V_{OH}	Output High voltage for P and N.	$R_T = 100\Omega$ across P and N signals	500	–	700	mV
V_{DDOUT}	Differential output voltage. (P–N), P = High (N–P), N = High	$R_T = 100\Omega$ across P and N signals	300	–	430	mV
V_{CMOUT}	Common mode voltage.	$R_T = 100\Omega$ across P and N signals	300	–	500	mV

Table 99: GTH Transceiver Reference Clock Switching Characteristics

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
F _{GCLK}	Reference clock frequency range.		60	–	820	MHz
T _{RCLK}	Reference clock rise time.	20% – 80%	–	200	–	ps
T _{FCLK}	Reference clock fall time.	80% – 20%	–	200	–	ps
T _{DCREF}	Reference clock duty cycle.	Transceiver PLL only	40	50	60	%

Table 100: GTH Transceiver Reference Clock Oscillator Selection Phase Noise Mask

Symbol	Description	Offset Frequency	Min	Typ	Max	Units
QPLL _{REFCLKMASK} ⁽¹⁾⁽²⁾	QPLL0/QPLL1 reference clock select phase noise mask at REFCLK frequency = 312.5 MHz.	10 kHz	–	–	–105	dBc/Hz
		100 kHz	–	–	–124	
		1 MHz	–	–	–130	
CPLL _{REFCLKMASK} ⁽¹⁾⁽²⁾	CPLL reference clock select phase noise mask at REFCLK frequency = 312.5 MHz.	10 kHz	–	–	–105	dBc/Hz
		100 kHz	–	–	–124	
		1 MHz	–	–	–130	
		50 MHz	–	–	–140	

Notes:

- For reference clock frequencies other than 312.5 MHz, adjust the phase-noise mask values by 20 x Log(N/312.5) where N is the new reference clock frequency in MHz.
- This reference clock phase-noise mask is superseded by any reference clock phase-noise mask that is specified in a supported protocol, e.g., PCIe.

Table 101: GTH Transceiver PLL/Lock Time Adaptation

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
T _{LOCK}	Initial PLL lock.		–	–	1	ms
T _{DLOCK}	Clock recovery phase acquisition and adaptation time for decision feedback equalizer (DFE).	After the PLL is locked to the reference clock, this is the time it takes to lock the clock data recovery (CDR) to the data present at the input.	–	50,000	37 x 10 ⁶	UI
	Clock recovery phase acquisition and adaptation time for low-power mode (LPM) when the DFE is disabled.		–	50,000	2.3 x 10 ⁶	UI

Table 102: GTH Transceiver User Clock Switching Characteristics⁽¹⁾

Symbol	Description	Data Width Conditions (Bit)		Speed Grade and V _{CCINT} Operating Voltages					Units
				0.90V	0.85V		0.72V		
		Internal Logic	Interconnect Logic	-3 ⁽²⁾	-2 ⁽²⁾⁽³⁾	-1 ⁽⁴⁾⁽⁵⁾	-2 ⁽³⁾	-1 ⁽⁵⁾	
F _{TXOUTPMA}	TXOUTCLK maximum frequency sourced from OUTCLKPMA			511.719	511.719	390.625	390.625	322.266	MHz
F _{RXOUTPMA}	RXOUTCLK maximum frequency sourced from OUTCLKPMA			511.719	511.719	390.625	390.625	322.266	MHz

Table 103: GTH Transceiver Transmitter Switching Characteristics

Symbol	Description	Condition	Min	Typ	Max	Units
F _{GTHTX}	Serial data rate range		0.500	–	F _{GTHMAX}	Gb/s
T _{RTX}	TX rise time	20%–80%	–	21	–	ps
T _{FTX}	TX fall time	80%–20%	–	21	–	ps
T _{LLSKEW}	TX lane-to-lane skew ⁽¹⁾		–	–	500.00	ps
T _{J16.375}	Total jitter ⁽²⁾⁽⁴⁾	16.375 Gb/s	–	–	0.28	UI
D _{J16.375}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J15.0}	Total jitter ⁽²⁾⁽⁴⁾	15.0 Gb/s	–	–	0.28	UI
D _{J15.0}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J14.1}	Total jitter ⁽²⁾⁽⁴⁾	14.1 Gb/s	–	–	0.28	UI
D _{J14.1}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J14.1}	Total jitter ⁽²⁾⁽⁴⁾	14.025 Gb/s	–	–	0.28	UI
D _{J14.1}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J13.1}	Total jitter ⁽²⁾⁽⁴⁾	13.1 Gb/s	–	–	0.28	UI
D _{J13.1}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J12.5_QPLL}	Total jitter ⁽²⁾⁽⁴⁾	12.5 Gb/s	–	–	0.28	UI
D _{J12.5_QPLL}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J12.5_CPLL}	Total jitter ⁽³⁾⁽⁴⁾	12.5 Gb/s	–	–	0.33	UI
D _{J12.5_CPLL}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.17	UI
T _{J11.3_QPLL}	Total jitter ⁽²⁾⁽⁴⁾	11.3 Gb/s	–	–	0.28	UI
D _{J11.3_QPLL}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J10.3125_QPLL}	Total jitter ⁽²⁾⁽⁴⁾	10.3125 Gb/s	–	–	0.28	UI
D _{J10.3125_QPLL}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J10.3125_CPLL}	Total jitter ⁽³⁾⁽⁴⁾	10.3125 Gb/s	–	–	0.33	UI
D _{J10.3125_CPLL}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.17	UI
T _{J9.953_QPLL}	Total jitter ⁽²⁾⁽⁴⁾	9.953 Gb/s	–	–	0.28	UI
D _{J9.953_QPLL}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J9.953_CPLL}	Total jitter ⁽³⁾⁽⁴⁾	9.953 Gb/s	–	–	0.33	UI
D _{J9.953_CPLL}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.17	UI
T _{J8.0}	Total jitter ⁽³⁾⁽⁴⁾	8.0 Gb/s	–	–	0.32	UI
D _{J8.0}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.17	UI
T _{J6.6}	Total jitter ⁽³⁾⁽⁴⁾	6.6 Gb/s	–	–	0.30	UI
D _{J6.6}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.15	UI
T _{J5.0}	Total jitter ⁽³⁾⁽⁴⁾	5.0 Gb/s	–	–	0.30	UI
D _{J5.0}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.15	UI
T _{J4.25}	Total jitter ⁽³⁾⁽⁴⁾	4.25 Gb/s	–	–	0.30	UI
D _{J4.25}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.15	UI
T _{J4.0}	Total jitter ⁽³⁾⁽⁴⁾	4.0 Gb/s	–	–	0.32	UI
D _{J4.0}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.16	UI
T _{J3.20}	Total jitter ⁽³⁾⁽⁴⁾	3.20 Gb/s ⁽⁵⁾	–	–	0.20	UI
D _{J3.20}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.10	UI

Table 115: GTY Transceiver Transmitter Switching Characteristics (Cont'd)

Symbol	Description	Condition	Min	Typ	Max	Units
T _{J3.20}	Total jitter ⁽³⁾⁽⁴⁾	3.20 Gb/s ⁽⁵⁾	–	–	0.20	UI
D _{J3.20}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.10	UI
T _{J2.5}	Total jitter ⁽³⁾⁽⁴⁾	2.5 Gb/s ⁽⁶⁾	–	–	0.20	UI
D _{J2.5}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.10	UI
T _{J1.25}	Total jitter ⁽³⁾⁽⁴⁾	1.25 Gb/s ⁽⁷⁾	–	–	0.15	UI
D _{J1.25}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.06	UI
T _{J500}	Total jitter ⁽³⁾⁽⁴⁾	500 Mb/s ⁽⁸⁾	–	–	0.10	UI
D _{J500}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.03	UI

Notes:

- Using same REFCLK input with TX phase alignment enabled for up to four consecutive transmitters (one fully populated GTY Quad) at maximum line rate.
- Using QPLL_FBDIV = 40, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
- Using CPLL_FBDIV = 2, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
- All jitter values are based on a bit-error ratio of 10⁻¹².
- CPLL frequency at 3.2 GHz and TXOUT_DIV = 2.
- CPLL frequency at 2.5 GHz and TXOUT_DIV = 2.
- CPLL frequency at 2.5 GHz and TXOUT_DIV = 4.
- CPLL frequency at 2.0 GHz and TXOUT_DIV = 8.

GTY Transceiver Electrical Compliance

The *UltraScale Architecture GTY Transceiver User Guide* ([UG578](#)) contains recommended use modes that ensure compliance for the protocols listed in [Table 117](#). The transceiver wizard provides the recommended settings for those use cases and for protocol specific characteristics.

Table 117: GTY Transceiver Protocol List

Protocol	Specification	Serial Rate (Gb/s)	Electrical Compliance
CAUI-4	IEEE 802.3-2012	25.78125	Compliant
28 Gb/s backplane	CEI-25G-LR	25–28.05	Compliant
Interlaken	OIF-CEI-6G, OIF-CEI-11GSR, OIF-CEI-28G-MR	4.25–25.78125	Compliant
100GBASE-KR4	IEEE 802.3bj-2014, CEI-25G-LR	25.78125	Compliant ⁽¹⁾
100GBASE-CR4	IEEE 802.3bj-2014, CEI-25G-LR	25.78125	Compliant ⁽¹⁾
50GBASE-KR4	IEEE 802.3by-2014, CEI-25G-LR	25.78125	Compliant ⁽¹⁾
50GBASE-CR4	IEEE 802.3by-2014, CEI-25G-LR	25.78125	Compliant ⁽¹⁾
25GBASE-KR4	IEEE 802.3by-2014, CEI-25G-LR	25.78125	Compliant ⁽¹⁾
25GBASE-CR4	IEEE 802.3by-2014, CEI-25G-LR	25.78125	Compliant ⁽¹⁾
OTU4 (OTL4.4) CFP2	OIF-CEI-28G-VSR	27.952493–32.75	Compliant
OTU4 (OTL4.4) CFP	OIF-CEI-11G-MR	11.18–13.1	Compliant
CAUI-10	IEEE 802.3-2012	10.3125	Compliant
nPPI	IEEE 802.3-2012	10.3125	Compliant
10GBASE-KR ⁽²⁾	IEEE 802.3-2012	10.3125	Compliant
SFP+	SFF-8431 (SR and LR)	9.95328–11.10	Compliant
XFP	INF-8077i, revision 4.5	10.3125	Compliant
RXAUI	CEI-6G-SR	6.25	Compliant
XAUI	IEEE 802.3-2012	3.125	Compliant
1000BASE-X	IEEE 802.3-2012	1.25	Compliant
5.0G Ethernet	IEEE 802.3bx (PAR)	5	Compliant
2.5G Ethernet	IEEE 802.3bx (PAR)	2.5	Compliant
HiGig, HiGig+, HiGig2	IEEE 802.3-2012	3.74, 6.6	Compliant
QSGMII	QSGMII v1.2 (Cisco System, ENG-46158)	5	Compliant
OTU2	ITU G.8251	10.709225	Compliant
OTU4 (OTL4.10)	OIF-CEI-11G-SR	11.180997	Compliant
OC-3/12/48/192	GR-253-CORE	0.1555–9.956	Compliant
PCIe Gen1, 2, 3	PCI Express base 3.0	2.5, 5.0, and 8.0	Compliant
SDI ⁽³⁾	SMPTE 424M-2006	0.27–2.97	Compliant
UHD-SDI ⁽³⁾	SMPTE ST-2081 6G, SMPTE ST-2082 12G	6 and 12	Compliant
Hybrid memory cube (HMC)	HMC-15G-SR	10, 12.5, and 15.0	Compliant
MoSys bandwidth engine	CEI-11-SR and CEI-11-SR (overclocked)	10.3125, 15.5	Compliant
CPRI	CPRI_v_6_1_2014-07-01	0.6144–12.165	Compliant
Passive optical network (PON)	10G-EPON, 1G-EPON, NG-PON2, XG-PON, and 2.5G-PON	0.155–10.3125	Compliant
JESD204a/b	OIF-CEI-6G, OIF-CEI-11G	3.125–12.5	Compliant

Table 124: PL SYSMON Specifications (Cont'd)

Parameter	Symbol	Comments / Conditions	Min	Typ	Max	Units
On-Chip Sensor Accuracy						
Temperature sensor error ⁽¹⁾⁽³⁾		$T_j = -55^{\circ}\text{C}$ to 125°C (with external REF)	–	–	± 3	$^{\circ}\text{C}$
		$T_j = -55^{\circ}\text{C}$ to 110°C (with internal REF)	–	–	± 3.5	$^{\circ}\text{C}$
		$T_j = 110^{\circ}\text{C}$ to 125°C (with internal REF)	–	–	± 5	$^{\circ}\text{C}$
Supply sensor error ⁽⁴⁾		Supply voltages 0.72V to 1.2V, $T_j = -40^{\circ}\text{C}$ to 100°C (with external REF)	–	–	± 0.5	%
		Supply voltages 0.72V to 1.2V, $T_j = -55^{\circ}\text{C}$ to 125°C (with external REF)	–	–	± 1.0	%
		All other supply voltages, $T_j = -40^{\circ}\text{C}$ to 100°C (with external REF)	–	–	± 1.0	%
		All other supply voltages, $T_j = -55^{\circ}\text{C}$ to 125°C (with external REF)	–	–	± 2.0	%
		Supply voltages 0.72V to 1.2V, $T_j = -40^{\circ}\text{C}$ to 100°C (with internal REF)	–	–	± 1.0	%
		Supply voltages 0.72V to 1.2V, $T_j = -55^{\circ}\text{C}$ to 125°C (with internal REF)	–	–	± 2.0	%
		All other supply voltages, $T_j = -40^{\circ}\text{C}$ to 100°C (with internal REF)	–	–	± 1.5	%
		All other supply voltages, $T_j = -55^{\circ}\text{C}$ to 125°C (with internal REF)	–	–	± 2.5	%
Conversion Rate⁽⁵⁾						
Conversion time—continuous	t_{CONV}	Number of ADCCLK cycles	26	–	32	Cycles
Conversion time—event	t_{CONV}	Number of ADCCLK cycles	–	–	21	Cycles
DRP clock frequency	DCLK	DRP clock frequency	8	–	250	MHz
ADC clock frequency	ADCCLK	Derived from DCLK	1	–	5.2	MHz
DCLK duty cycle			40	–	60	%
SYSMON Reference⁽⁶⁾						
External reference	V_{REFP}	Externally supplied reference voltage	1.20	1.25	1.30	V
On-chip reference		Ground V_{REFP} pin to AGND, $T_j = -40^{\circ}\text{C}$ to 100°C	1.2375	1.25	1.2625	V
		Ground V_{REFP} pin to AGND, $T_j = -55^{\circ}\text{C}$ to 125°C	1.225	1.25	1.275	V

Notes:

- ADC offset errors are removed by enabling the ADC automatic offset calibration feature. The values are specified for when this feature is enabled.
- See the *Analog Input* section in the *UltraScale Architecture System Monitor User Guide* ([UG580](#)).
- When reading temperature values directly from the PMBus interface, the SYSMON has a $+4^{\circ}\text{C}$ offset due to the transfer function used by the PMBus application. For example, the external REF temperature sensor error's range of $\pm 3^{\circ}\text{C}$ becomes $+1^{\circ}\text{C}$ to $+7^{\circ}\text{C}$ when the temperature is read through the PMBus interface.
- Supply sensor offset and gain errors are removed by enabling the automatic offset and gain calibration feature. The values are specified for when this feature is enabled.
- See the *Adjusting the Acquisition Settling Time* section in the *UltraScale Architecture System Monitor User Guide* ([UG580](#)).
- Any variation in the reference voltage from the nominal $V_{\text{REFP}} = 1.25\text{V}$ and $V_{\text{REFN}} = 0\text{V}$ will result in a deviation from the ideal transfer function. This also impacts the accuracy of the internal sensor measurements (i.e., temperature and power supply). However, for external ratiometric type applications allowing reference to vary by $\pm 4\%$ is permitted.

PL SYSMON I2C/PMBus Interfaces

Table 125: PL SYSMON I2C Fast Mode Interface Switching Characteristics⁽¹⁾

Symbol	Description	Min	Max	Units
T_{SMFCKL}	SCL Low time	1.3	–	μ s
T_{SMFCKH}	SCL High time	0.6	–	μ s
T_{SMFCKO}	SDAO clock-to-out delay	–	900	ns
T_{SMFDCK}	SDAI setup time	100	–	ns
F_{SMFCLK}	SCL clock frequency	–	400	kHz

Notes:

1. The test conditions are configured to the LVCMOS 1.8V I/O standard.

Table 126: PL SYSMON I2C Standard Mode Interface Switching Characteristics⁽¹⁾

Symbol	Description	Min	Max	Units
T_{SMSCKL}	SCL Low time	4.7	–	μ s
T_{SMSCKH}	SCL High time	4.0	–	μ s
T_{SMSCKO}	SDAO clock-to-out delay	–	3450	ns
T_{SMSDCK}	SDAI setup time	250	–	ns
F_{SMSCLK}	SCL clock frequency	–	100	kHz

Notes:

1. The test conditions are configured to the LVCMOS 1.8V I/O standard.